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CLAIMS

- 1. A process for the selective removal of sulphur compounds from synthesis gas containing at least 5% carbon monoxide, at least 5% hydrogen and at least 0.5% carbon divide and optionally containing water in a concentration up to saturation at a pressure of at least 15 bar comprising contacting the synthesis gas at a maximum contact temperature of 100°C with an absorbent comprising Cu/ZnO compounds and activated with a reducing gas.
- 2. Process of claim 1, wherein the sulphur compounds comprise H_2S and COS.
- 3. Process according to any one of the preceding claims, wherein the synthesis gas contains H_2S in an amount effective for suppression of metal dusting of metals in contact with the synthesis gas within a temperature range between 300°C to Boudouard temperature of the synthesis gas.